

BC327/328

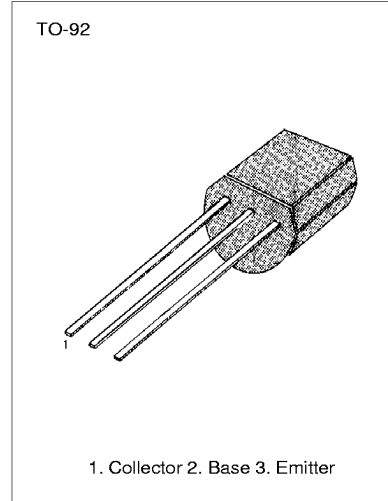
PNP EPITAXIAL SILICON TRANSISTOR

SWITCHING AND AMPLIFIER APPLICATIONS

- Suitable for AF-Driver stages and low power output stages
- Complement to BC337/BC338

ABSOLUTE MAXIMUM RATINGS (T_A=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Emitter Voltage : BC327	V _{CES}	-50	V
: BC328		-30	V
Collector-Emitter Voltage : BC327	V _{CEO}	-45	V
: BC328		-25	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current (DC)	I _C	-800	mA
Collector Dissipation	P _C	625	mW
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-55 ~ 150	°C



ELECTRICAL CHARACTERISTICS (T_A=25°C)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Emitter Breakdown Voltage : BC327	BV _{CEO}	I _C = -10mA, I _B =0	-45			V
: BC328			-25			V
Collector Emitter Breakdown Voltage : BC327	BV _{CES}	I _C = -0.1mA, I _B =0	-50			V
: BC328			-30			V
Emitter Base Breakdown Voltage	BV _{EBO}	I _E = -10mA, I _C =0	-5			V
Collector Cut-off Current : BC307	I _{CES}	V _{CE} = -45V, I _B =0		-2	-100	nA
: BC338			V _{CE} = -25V, I _B =0		-2	-100
DC Current Gain	h _{FE}	V _{CE} = -1V, I _C = -100mA	100		630	
	h _{FE2}	V _{CE} = -1V, I _C = -30mA	60			
Collector-Emitter Saturation Voltage	V _{CE} (sat)	I _C = -500mA, I _B = -50mA			-0.7	V
Base Emitter On Voltage	V _{BE} (on)	V _{CE} = -1V, I _C = -300mA			-1.2	V
Current Gain Bandwidth Product	f _T	V _{CE} = -5V, I _C = -10mA		100		MHz
Collector Base Capacitance	C _{CB0}	V _{CB} = -10V, f=1MHz		12		pF

h_{FE} CLASSIFICATION

Classification	A	B	C
h _{FE}	100-250	160-400	250-630
h _{FE2}	60-	100-	170-

